

AMENDMENT TO THE SPECIFICATION

Please replace the paragraph on page 20, beginning with line 13, with the following paragraph:

FIG. 2 is a cross-sectional view of a part of a semiconductor device according to a first embodiment of the present invention. As shown in FIG. ~~[[1]]~~ 2, three kinds of wells 5, 12, 20 are formed on a surface of a P-type ~~silicone~~ silicon substrate 10. The well 20 is an N-well (NW), which is formed by introducing or doping N-type impurities. The well 5 is a lightly-N-well (Lightly-NW), of which impurity concentration is lower than that of the N-well 20. The N-well 20 and the lightly-N-well 5 are separated from each other. Each of the wells 12 is a P-well (PW), which is formed by introducing or doping P-type impurities at a concentration higher than the impurity concentration of the substrate 10. The P-wells 12 are formed in a self-aligning manner in the vicinity of the wells 5 and 20.

Please replace the paragraph on page 22, beginning with line 12, with the following paragraph:

A field oxide film 30 for separating elements is formed in a boundary area between the wells. A MOS transistor is formed in the well of an element area separated by the field oxide film 30. The P-well 12 on the left side in FIG. ~~[[1]]~~ 2 is provided with a source 34 and a drain 36 that are formed by N-type diffusion layers, and a gate electrode 32 of a polysilicon is formed on an area between the diffusion layers 34 and 36 via a gate oxide film 31, which together constitute an N-channel MOS transistor.